Nikolay I Gorbachuk

List of Publications by Year in descending order

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1307594 1372567 21 113 7 10 citations g-index h-index papers 21 21 21 85 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Negative capacitance (impedance of the inductive type) of silicon p +-n junctions irradiated with fast electrons. Semiconductors, 2006, 40, 803-807.	0.5	14
2	Formation of coloring complexes in glass colored with cerium and titanium oxides. Glass and Ceramics (English Translation of Steklo I Keramika), 2007, 64, 346-348.	0.6	11
3	Electrical properties of silicon diodes with p+n junctions irradiated with 197Au+26 swift heavy ions. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 5007-5012.	1.4	10
4	Equivalent circuit of silicon diodes subjected to high-fluence electron irradiation. Technical Physics, 2010, 55, 1463-1471.	0.7	9
5	Impedance and barrier capacitance of silicon diodes implanted with high-energy Xe ions. Microelectronics Reliability, 2010, 50, 813-820.	1.7	9
6	IMPEDANCE SPECTROSCOPY OF POLYCRYSTALLINE TIN DIOXIDE FILMS. Pribory I Metody Izmerenij, 2016, 7, 312-321.	0.3	8
7	Electrical Conductivity of Composite Materials Based on Fine-Particle Silicon near the Metal–Insulator Transition. Inorganic Materials, 2004, 40, 1133-1138.	0.8	7
8	Nanostructuring of crystalline grains of natural diamond using ionizing radiation. Semiconductors, 2005, 39, 894-897.	0.5	7
9	Magnetoresistive effect and impedance spectroscopy of Co-implanted polyimide. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1545-1549.	1.8	7
10	Kinetics of reverse resistance recovery of silicon diodes: The role of the distance the metallurgical p+n-junction-defect layer formed by 250MeV krypton implantation. Physica B: Condensed Matter, 2009, 404, 4667-4670.	2.7	6
11	Optical spectroscopy of the surface of nanoporous diamond films. Journal of Applied Spectroscopy, 2011, 78, 563-571.	0.7	6
12	Effect of the Moisture Content on the Electrical Conductivity of SiO2/LiCl Xerogels. Glass Physics and Chemistry, 2001, 27, 520-526.	0.7	4
13	Impedance of Single-Walled Carbon Nanotube Fibers. Fullerenes Nanotubes and Carbon Nanostructures, 2012, 20, 434-438.	2.1	4
14	Effects of Fluences of Irradiation with 107 MeV Krypton lons on the Recovery Charge of Silicon p ⁺ n-Diodes. Acta Physica Polonica A, 2011, 120, 111-114.	0.5	4
15	Impedance of Si/SiO2 composites in the vicinity of the percolation threshold. Physics of the Solid State, 2011, 53, 462-466.	0.6	3
16	The dependence of the conductivity of SiO2- \hat{l}^3 -Fe2O3 film composites on air humidity. Russian Journal of Physical Chemistry A, 2010, 84, 684-688.	0.6	2
17	Influence of radiation defects on electrical losses in silicon diodes irradiated with electrons. Semiconductors, 2010, 44, 380-384.	0.5	2
18	X-ray-Induced Paramagnetic Centers in SiO2Xerogels. Inorganic Materials, 2001, 37, 482-486.	0.8	0

#	Article	IF	CITATIONS
19	Current-Voltage Characteristic Features of Diodes Irradiated with 170–MeV Xenon Ions. Acta Physica Polonica A, 2013, 123, 926-928.	0.5	0
20	AC-Conductivity of Thin Polycrystalline Tin Dioxide Films. Acta Physica Polonica A, 2011, 119, 146-147.	0.5	0
21	Influence of Defects Introduced by Irradiation with 4-9 MeV Helium Ions on Impedance of Silicon Diodes. Acta Physica Polonica A, 2015, 128, 891-894.	0.5	0